Docket No. 0819-0703

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of	)	Art Unit: Unassigned
Yoshiaki HASEGAWA et al.	)	Examiner: Unassigned
Serial No. 09/993,771	)	
Filed: November 27, 2001	)	
For: METHOD FOR MANUFACTURING SEMICONDUCTOR AND METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE	)	

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on 3/21/02

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the above identified patent application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

On Page 27, First Full Paragraph

Thus, according to the second variation, the etching stop layer **19C** having a super lattice structure is formed under the p-type second cladding layer **20** to be etched, whereby it is possible to control the thickness (remaining thickness) of the p-type first cladding layer **18** with a high precision. As a result, it is possible to obtain a desired thickness, i.e., an optimal value, for the thickness of the p-type first cladding layer **18**. Therefore, the light confinement efficiency in the MQW active layer **15** is significant improved. This is because of the prevention of an etching damage to the MQW active layer **15**.

On Page 30, Fourth Paragraph continuing on Page 31

As illustrated in FIG. **10**, during the etching process on the p-type second cladding layer **20**, which is made of p-type $Al_{0.07}Ga_{0.93}N$, the wavelength of the detected PL light is about 350